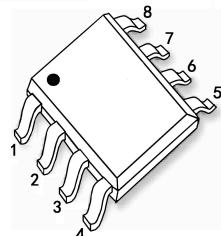


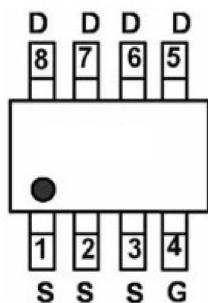
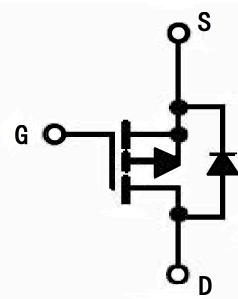
FEATURES

- $R_{DS(ON)} \leq 55\text{m}\Omega$ (43 $\text{m}\Omega$ Typ.) @ $V_{GS} = -10\text{V}$
- $R_{DS(ON)} \leq 90\text{m}\Omega$ (55 $\text{m}\Omega$ Typ.) @ $V_{GS} = -4.5\text{V}$

SOP-8**APPLICATIONS**

- PWM Applications
- Load Switch
- Power Management

1: S	3: S	5: D	7: D
2: S	4: G	6: D	8: D

PIN ASSIGNMENT**P-CHANNEL MOSFET****Absolute maximum ratings (Ta=25°C unless otherwise noted)**

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		± 20	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	-5.1	A
		$T_C = 100^\circ\text{C}$	-3.2	A
I_{DM}	Pulsed Drain Current ^{note1}		-20	A
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$	2.5	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		50	$^\circ\text{C}/\text{W}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	$^\circ\text{C}$

Electrical characteristics ($T_a=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D = -250\mu\text{A}$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$	-1	-1.35	-2	V
$R_{\text{DS}(\text{on})}$	Static Drain-Source on-Resistance note2	$V_{GS} = -10\text{V}, I_D = -5.1\text{A}$	-	43	55	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}, I_D = -4.2\text{A}$	-	55	90	
g_{FS}	Forward Transconductance	$V_{DS} = -5\text{V}, I_D = -5.1\text{A}$	4	-	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	-	980	-	pF
C_{oss}	Output Capacitance		-	390	-	pF
C_{rss}	Reverse Transfer Capacitance		-	135	-	pF
Q_g	Total Gate Charge	$V_{DS} = -15\text{V}, I_D = -5.1\text{A}, V_{GS} = -10\text{V}$	-	11	-	nC
Q_{gs}	Gate-Source Charge		-	2.0	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	2.8	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = -15\text{V}, I_D = -1\text{A}, V_{GS} = -10\text{V}, R_{\text{GEN}} = 6\Omega$	-	14	-	ns
t_r	Turn-on Rise Time		-	12	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	56	-	ns
t_f	Turn-off Fall Time		-	20	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_s	Maximum Continuous Drain to Source Diode Forward Current	-	-	-5.1	-	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	-20	-	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}, I_s = -5.1\text{A}$	-	-	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$

Typical Characteristics

Figure 1: Output Characteristics

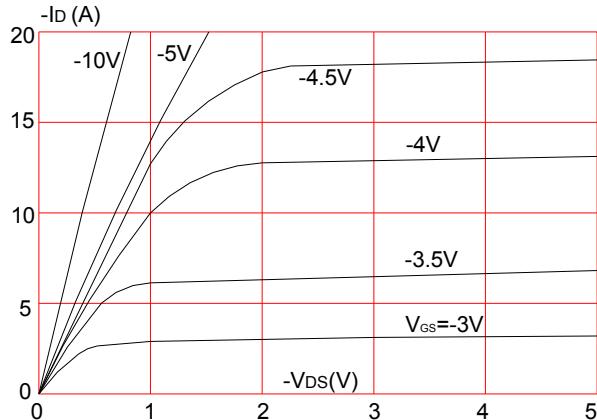


Figure 2: Typical Transfer Characteristics

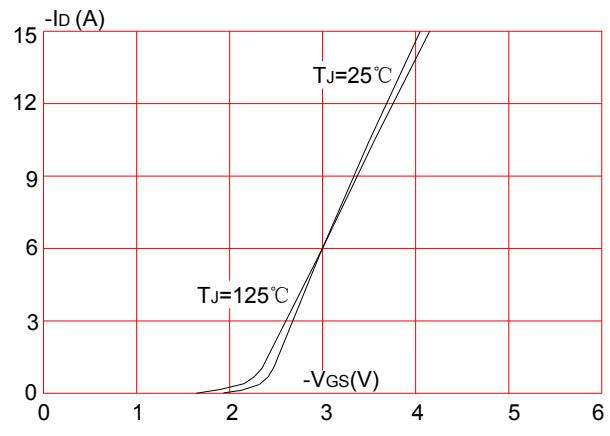


Figure 3: On-resistance vs. Drain Current

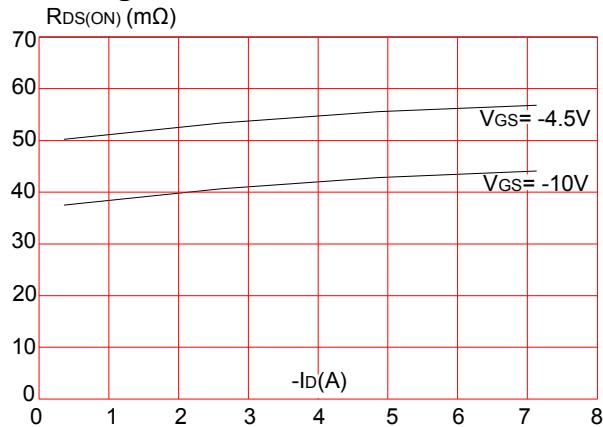


Figure 5: Gate Charge Characteristics

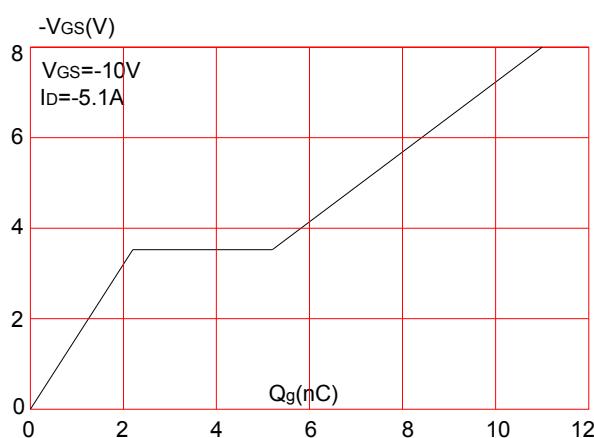


Figure 4: Body Diode Characteristics

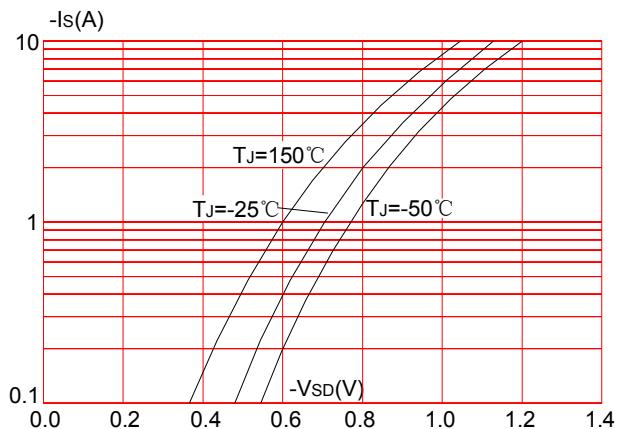
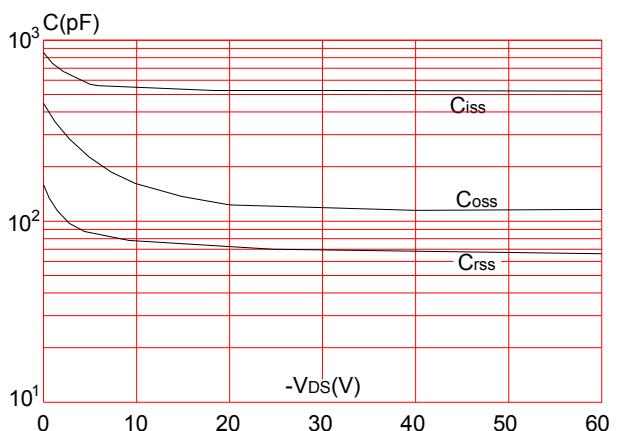


Figure 6: Capacitance Characteristics



Typical Characteristics

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

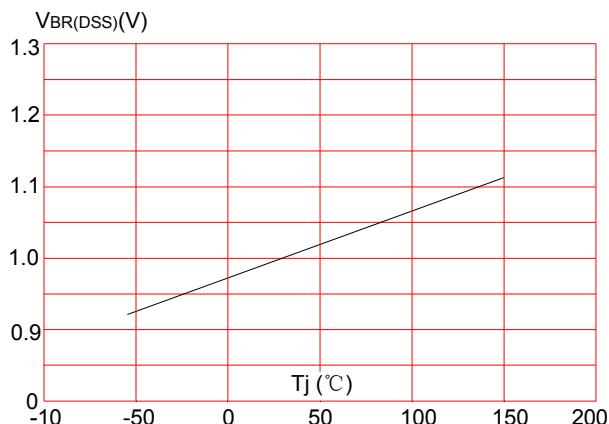


Figure 8: Normalized on Resistance vs. Junction Temperature

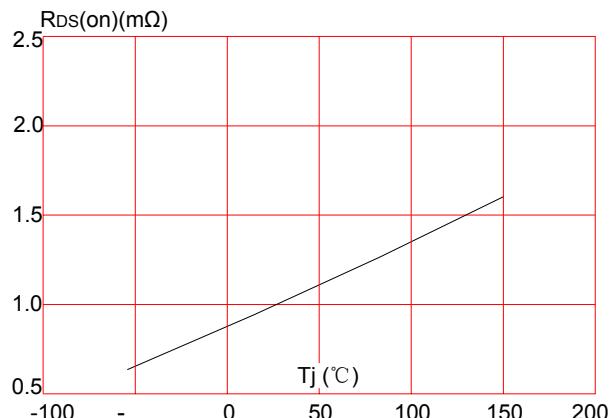


Figure 9: Maximum Safe Operating Area

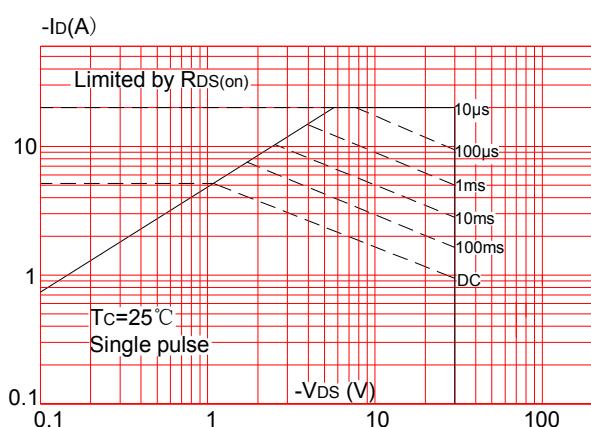


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

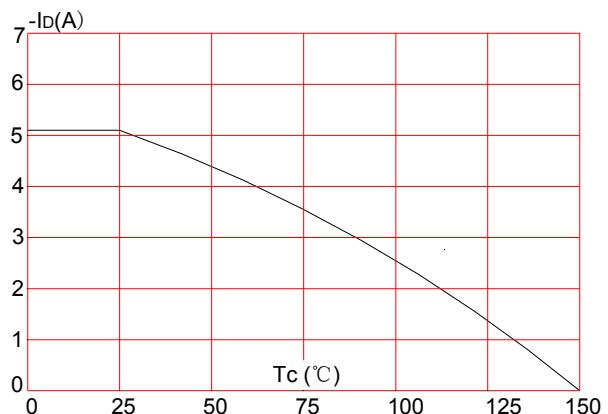
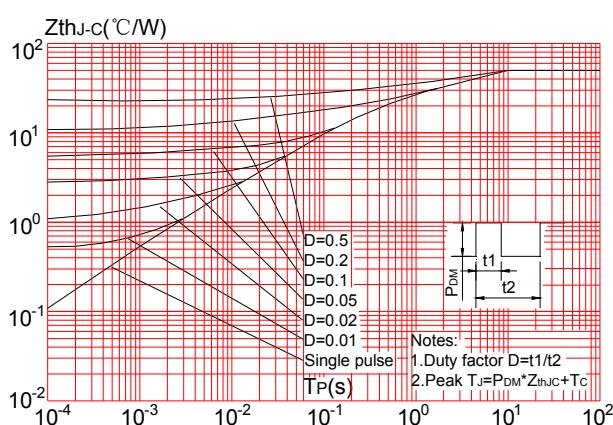
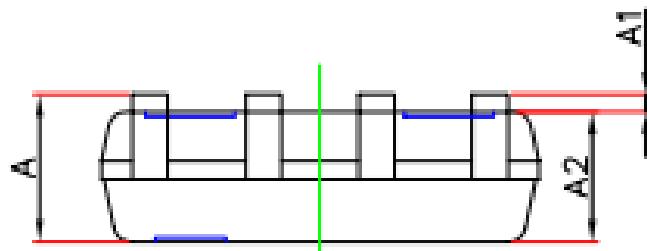
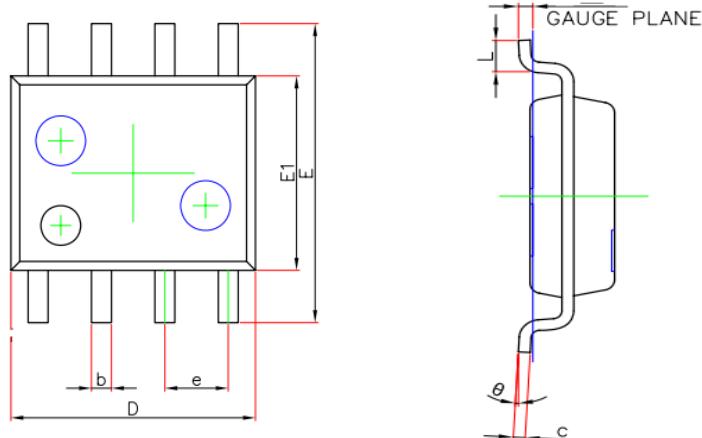


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient (SOP-8)



SOP-8 PACKAGE OUTLINE DRAWING



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E1	3.800	4.000	0.150	0.157
E	5.800	6.200	0.228	0.244
e	1.27(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

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